CLAIMS

1. A sputtering target comprising:

10 mol% or more and 85 mol% or less of Co, 0 mol% or more and 47 mol% or less of Pt, and 0 mol% or more and 47 mol% or less of Cr, as metal components; and

at least B_6O as an oxide component,

wherein an amount of B eluted is 1000 μg/L/cm^2 or less.

2. The sputtering target according to claim 1, wherein B_6O is contained an amount of 0.1 mol% or more and 10 mol% or less.

3. The sputtering target according to claim 1 or 2, comprising an oxide of at least one selected from the group consisting of Cr, Ta, Ti, Si, Zr, Al, Nb, B and Co as an oxide component, and wherein a volume ratio of the total oxide to the total sputtering target is 1 mol% or more and 20 mol% or less.

4. The sputtering target according to any one of claims 1 to 3, comprising an additive element component selected from the group consisting of B, N, Ti, V, Mn, Zr, Nb, Ru, Mo, Ta, W, Si and Al in a total amount of 35 mol% or less.

5. ~~The sputtering target according to any one of claims 1 to 4, wherein an amount of B eluted is 1000 μg/L/cm^2 or less.~~

~~6.~~ The sputtering target according to any one of claims 1 to ~~5~~4, wherein the sputtering target has a diffraction peak of B_6O (110) in a range of 2θ = 30 to 35° and

a diffraction peak of B_6O (104) in a range of 2θ = 35 to 40° in an XRD diffraction pattern using Cu as a radiation source.

~~7~~6. A method for producing a sputtering target comprising:

preparing 10 mol% or more and 85 mol% or less of Co, 0 mol% or more and 47 mol% or less of Pt, and 0 mol% or more and 47 mol% or less of Cr as metal powder;

adding B_6O in the form of oxide powder to the metal powder to mix them; and

sintering the mixed powder to produce a sputtering target in which an amount of B eluted is 1000 μg/L/cm^2 or less.

~~8~~7. The method for producing a sputtering target according to claim ~~7~~6, wherein a sintering temperature is from 700 °C to 1200 °C.